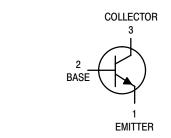
MPS2222A is a Preferred Device

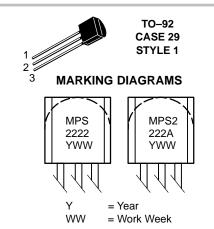
General Purpose Transistors

NPN Silicon



http://onsemi.com





MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MPS2222 MPS2222A	VCEO	30 40	Vdc
Collector–Base Voltage MPS2222 MPS2222A	VCBO	60 75	Vdc
Emitter–Base Voltage MPS2222 MPS2222A	V _{EBO}	5.0 6.0	Vdc
Collector Current – Continuous	IC	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	83.3	°C/W

ORDERING INFORMATION

Device	Package Shipping	
MPS2222	TO-92	5000 Units/Box
MPS2222A	TO-92	5000 Units/Box
MPS2222ARLRA	TO-92	2000/Tape & Reel
MPS2222ARLRM	TO-92	2000/Ammo Pack
MPS2222ARLRP	TO-92	2000/Ammo Pack
MPS2222RLRA	TO-92	2000/Tape & Reel
MPS2222RLRM	TO-92	2000/Ammo Pack
MPS2222RLRP	TO-92	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		'		•	
Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	MPS2222 MPS2222A	V(BR)CEO	30 40	_ _	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	MPS2222 MPS2222A	V(BR)CBO	60 75	_ _	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	MPS2222 MPS2222A	V _{(BR)EBO}	5.0 6.0	_ _	Vdc
Collector Cutoff Current (VCE = 60 Vdc, VEB(off) = 3.0 Vdc)	MPS2222A	ICEX	-	10	nAdc
Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0) (V _{CB} = 60 Vdc, I _E = 0) (V _{CB} = 50 Vdc, I _E = 0, T _A = 125°C) (V _{CB} = 50 Vdc, I _E = 0, T _A = 125°C)	MPS2222 MPS2222A MPS2222 MPS2222A	ICBO	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (VEB = 3.0 Vdc, I _C = 0)	MPS2222A	IEBO	-	100	nAdc
Base Cutoff Current (VCE = 60 Vdc, VEB(off) = 3.0 Vdc)	MPS2222A	I _{BL}	-	20	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{l} (I_{C}=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_{C}=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_{C}=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_{C}=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc, } T_{A}=-55^{\circ}\text{C}) \\ (I_{C}=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc) (Note 1.)} \\ (I_{C}=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc) (Note 1.)} \\ (I_{C}=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc) (Note 1.)} \\ \end{array} $	MPS2222A only MPS2222 MPS2222A	hFE	35 50 75 35 100 50 30 40	- - - 300 - -	-
Collector–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc)	MPS2222 MPS2222A	VCE(sat)	_ _	0.4 0.3	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MPS2222 MPS2222A		- -	1.6 1.0	
Base–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc)	MPS2222 MPS2222A	V _{BE} (sat)	_ 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MPS2222 MPS2222A			2.6 2.0	

^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2\%$.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic			Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERIST	CS				•	•
Current–Gain – Bandwidth Product (Not (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100	•	MPS2222 MPS2222A	fΤ	250 300	_ _	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E :	= 0, f = 1.0 MHz)		C _{obo}	-	8.0	pF
(LD		MPS2222 MPS2222A	C _{ibo}	- -	30 25	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0		MPS2222A MPS2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0		MPS2222A MPS2222A	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ Vdc}$		MPS2222A MPS2222A	h _{fe}	50 75	300 375	_
Output Admittance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0		MPS2222A MPS2222A	h _{Oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (I _E = 20 mAdc, V _{CB} = 20 Vdc, f = 31.	8 MHz)	MPS2222A	rb′C _C	-	150	ps
Noise Figure (I _C = 100 μ Adc, V _{CE} = 10 Vdc, R _S =	1.0 kΩ, f = 1.0 kHz)	MPS2222A	NF	-	4.0	dB
SWITCHING CHARACTERISTICS	MPS2222A only		1		1	
Delay Time	(V _{CC} = 30 Vdc, V _{BE(off)} = -0.5 Vdc, I _C = 150 mAdc, I _{B1} = 15 mAdc) (Figure 1)		t _d	-	10	ns
Rise Time			t _r	_	25	ns
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc,		t _S	_	225	ns

^{2.} f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

 $I_{B1} = I_{B2} = 15 \text{ mAdc}$) (Figure 2)

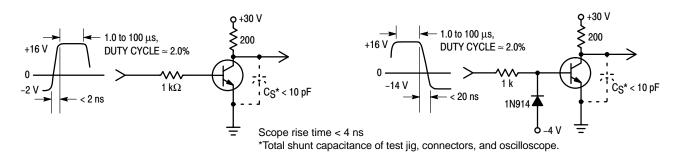


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

Fall Time

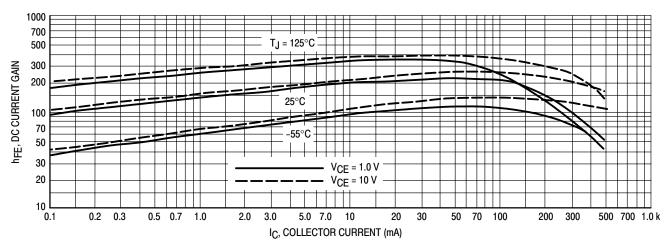


Figure 3. DC Current Gain

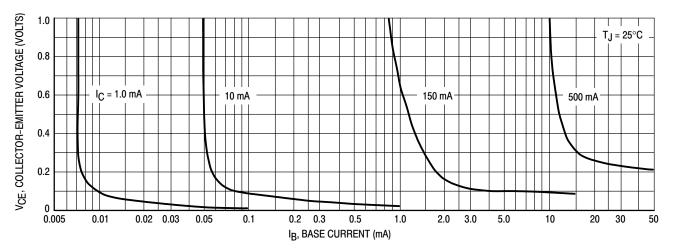


Figure 4. Collector Saturation Region

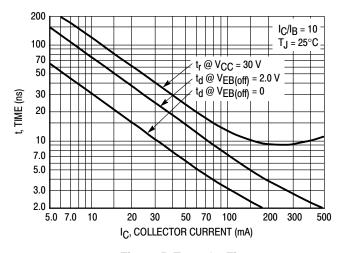


Figure 5. Turn-On Time

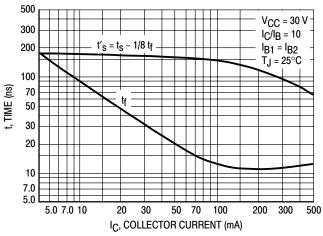


Figure 6. Turn-Off Time

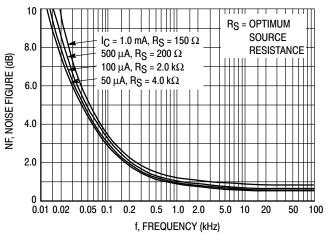


Figure 7. Frequency Effects

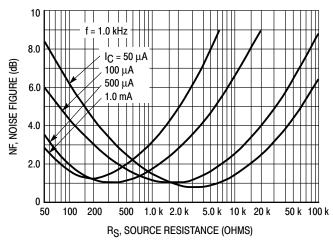


Figure 8. Source Resistance Effects

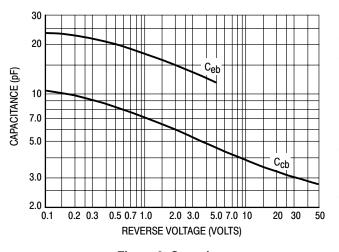


Figure 9. Capacitances

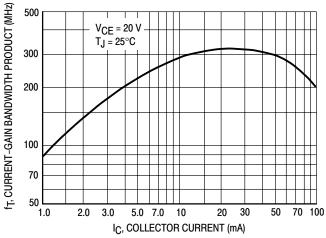
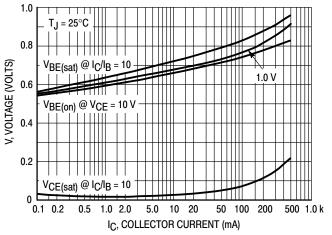
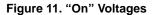


Figure 10. Current-Gain Bandwidth Product





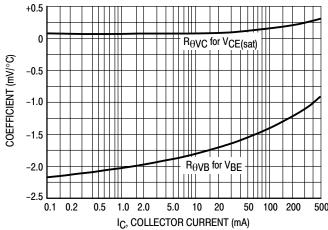
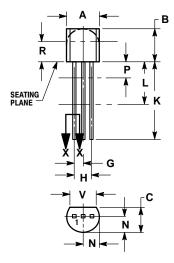


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 **TO-226AA** CASE 29-11 **ISSUE AL**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031

Phone: 81–3–5740–2700 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.

MPS2222/D